

## 1. Scope

The present specifications shall apply to an SJPX-H6.

## 2. Outline

Type	Silicon Diode
Structure	Resin Molded
Applications	High Frequency Rectification

## 3. Flammability

UL94V-0(Equivalent)

## 4. Absolute maximum ratings

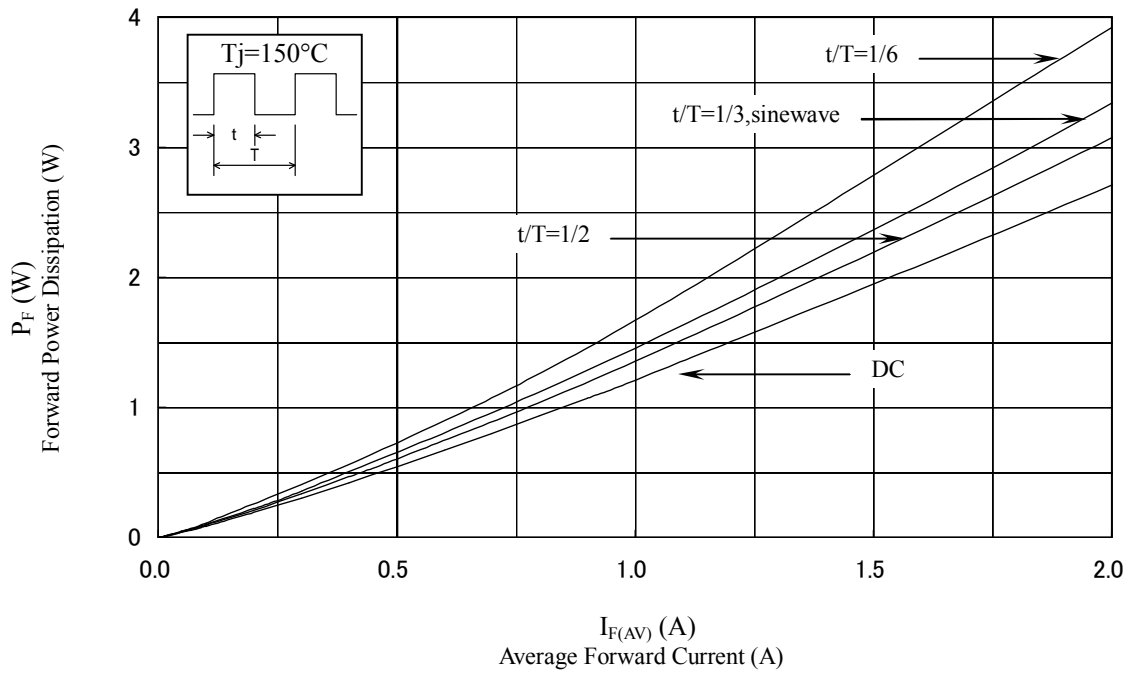
No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	$V_{RSM}$	V	600	
2	Peak Reverse Voltage	$V_{RM}$	V	600	
3	Average Forward Current	$I_{F(AV)}$	A	2.0	Refer to Derating of 7
4	Peak Surge Forward Current	$I_{FSM}$	A	20	10msec. Half sinewave, one shot
5	$I^2t$ Limiting Value	$I^2t$	$A^2s$	2.0	$1msec \leq t \leq 10msec$
6	Junction Temperature	$T_j$	$^{\circ}C$	-40~+150	
7	Storage Temperature	$T_{stg}$	$^{\circ}C$	-40~+150	

5. Electrical characteristics ( $T_a=25^{\circ}C$  , unless otherwise specified)

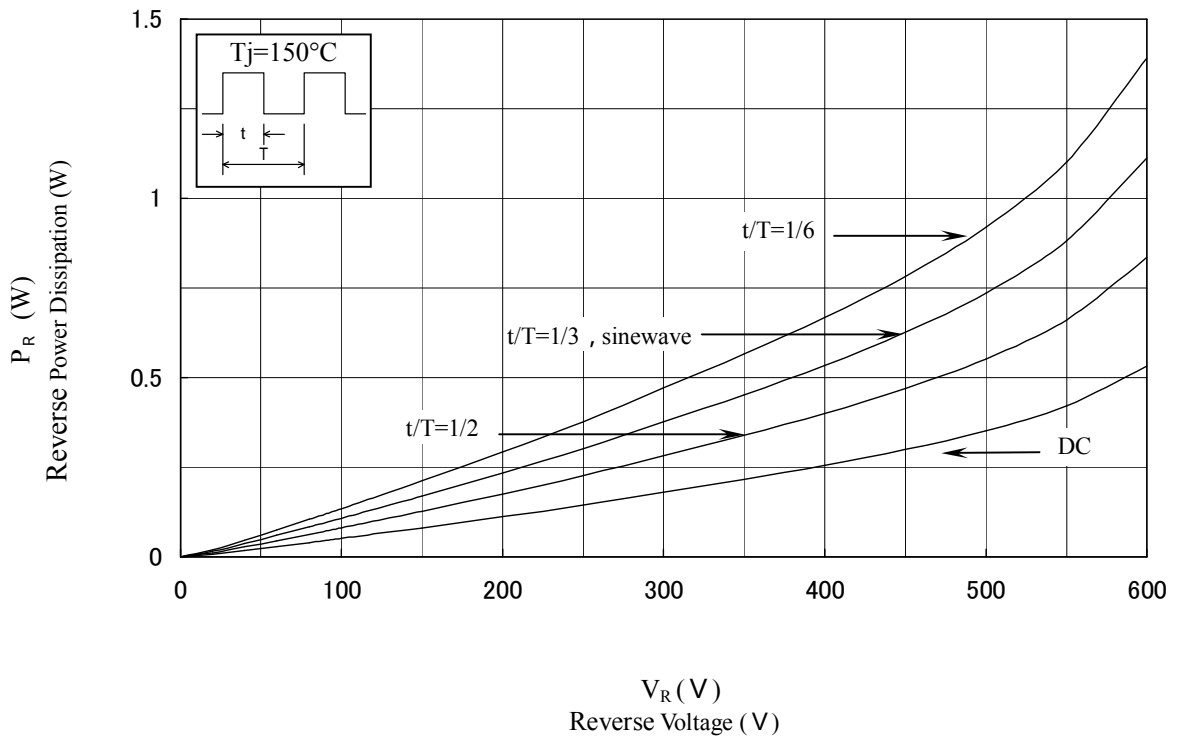
No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	$V_F$	V	1.5 max.	$I_F=2.0A$
2	Reverse Leakage Current	$I_R$	$\mu A$	10 max.	$V_R=V_{RM}$
3	Reverse Leakage Current Under High Temperature	$H \cdot I_R$	mA	3.0 max.	$V_R=V_{RM}, T_j=150^{\circ}C$
4	Reverse Recovery Time	$t_{rr1}$	ns	30 max.	$I_F=I_{RP}=100mA$ 95% Recovery point, $T_j=25^{\circ}C$
		$t_{rr2}$	ns	20 max.	$I_F=100mA, I_{RP}=200mA$ 75% Recovery point, $T_j=25^{\circ}C$
5	Thermal Resistance	$R_{th(j-l)}$	$^{\circ}C/W$	20 max.	Between Junction and lead

6. Characteristics

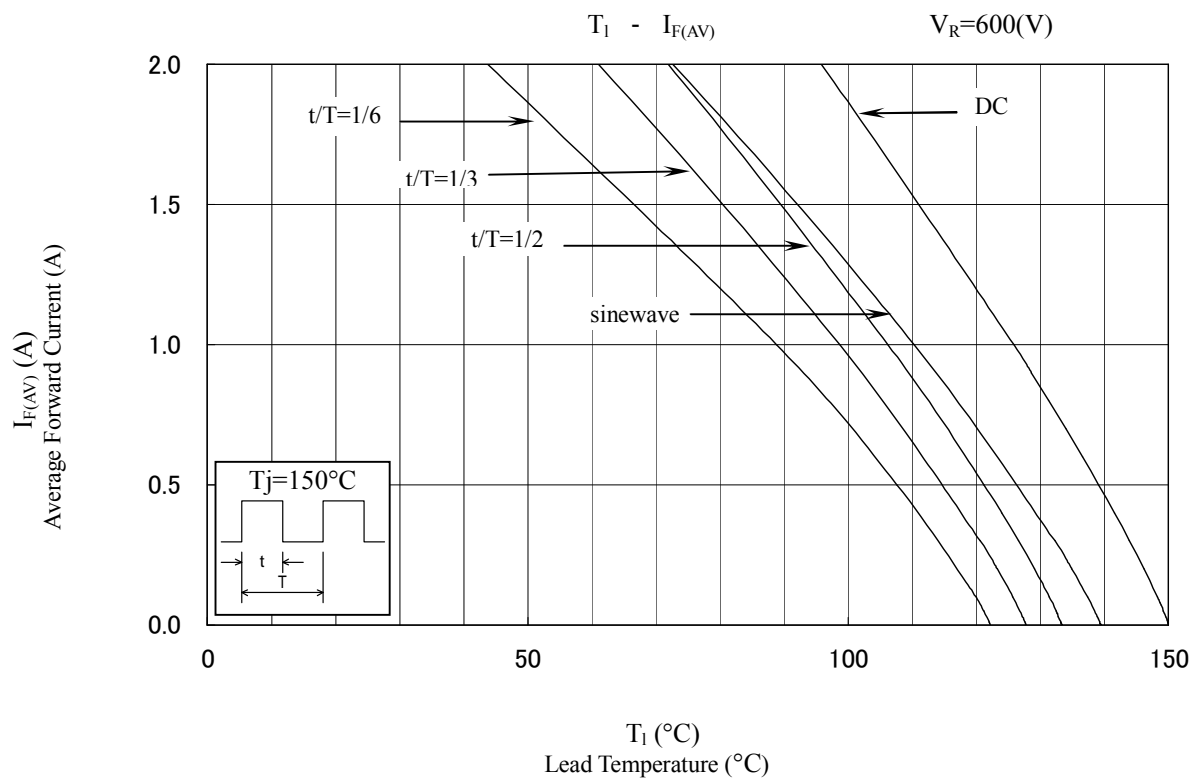
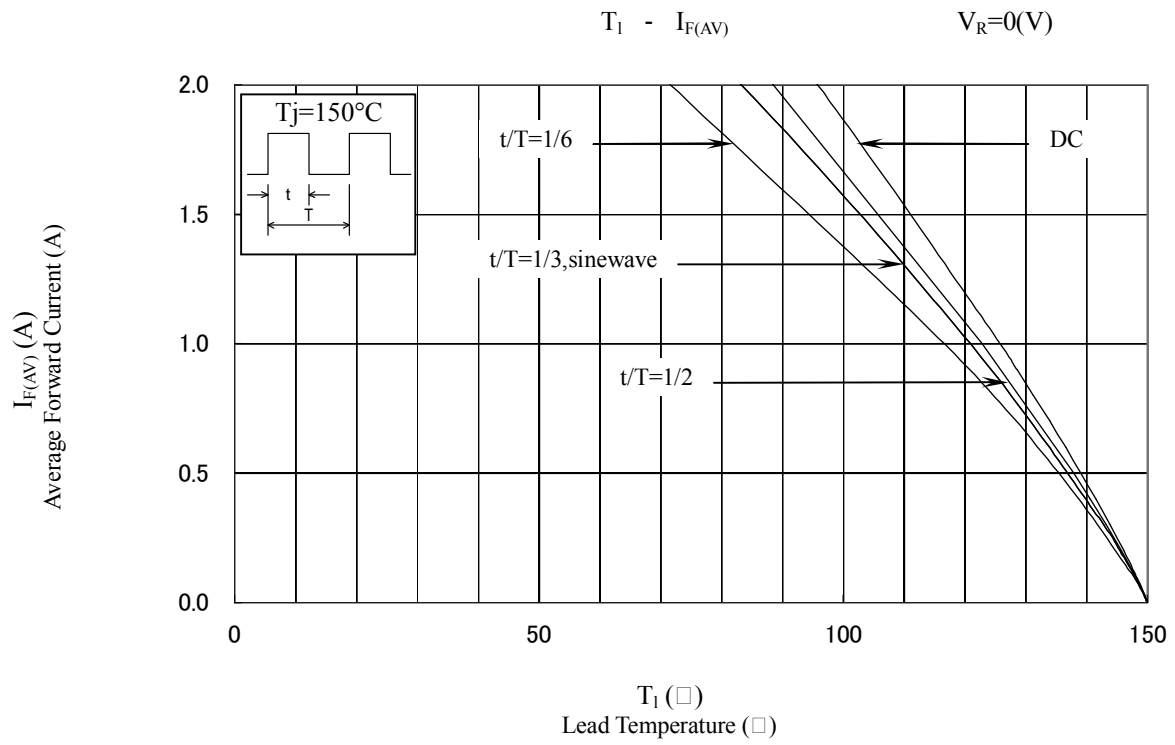
$I_{F(AV)} - P_F$



$V_R - P_R$

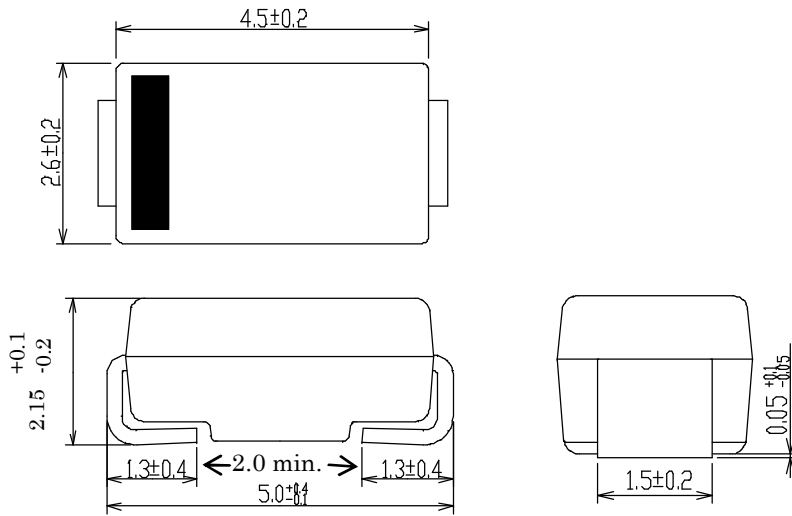


7.  
7 Derating



8. 8 Package information

8-1 Package type, physical dimensions and material



Dimensions in mm

8-2 Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

8-3 Marking

Polarity marking (Cathode band)

Type number  
SJPX-H6 as abbreviated of XH6

Lot number  
Example) 7220  
7: Last number of Year  
2: Month from 1 to 9 for Jan. to Sep.  
O for Oct. , N for Nov. , D for Dec.  
14: Day

